

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	3395	etch\$3 with pillar	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/12/09 17:17
L2	246	L1 and etch\$3 with strip	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/12/09 17:05
L3	26	L2 and second adj etch\$3 with pillar	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/12/09 17:17
L4	2	("20020028541").PN.	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/12/09 17:05
L5	21	L3 and antifuse	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/12/09 17:05

### EAST Search History

L6	263959	((first with (mask or photoresist or resist or pattern)) same (second with (mask or resist or photoresist or pattern)))	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/12/09 17:05
L7	42311	((first with (mask or photoresist or resist or pattern)) same (second with (mask or resist or photoresist or pattern)) same different)	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/12/09 17:05
L8	0	((first with (mask or photoresist or resist or pattern)) same (second with (mask or resist or photoresist or pattern)) same different same (back adj to adj back))	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/12/09 17:05
L9	1693	((first with (mask or photoresist or resist or pattern)) same (second with (mask or resist or photoresist or pattern)) same different same (sequential\$3))	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/12/09 17:05
L10	649	((first with (mask or photoresist or resist or pattern)) same (second with (mask or resist or photoresist or pattern)) same different same (sequential\$3)) and semiconductor	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/12/09 17:05

### EAST Search History

L11	95	((first adj (mask or photoresist or resist or pattern)) same (second adj (mask or resist or photoresist or pattern)) same different same (sequential\$3)) and semiconductor	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/12/09 17:05
L12	0	L11 and antifuse	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/12/09 17:05
L13	6	L11 and pillar	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/12/09 17:08
L14	1483	pillar with memory	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/12/09 17:05
L15	6	L13 and semiconductor and etch\$4	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/12/09 17:05

### EAST Search History

L16	939	L14 and semiconductor and etch\$4	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/12/09 17:05
L17	48	pillar with memory and etch\$4 with second adj direction	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/12/09 17:05
L18	267276	L1 L2 L3 L4 L5 L6 L7 L8 L9 L10 L11 L12 L13 L14 L15 L16 L17	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/12/09 17:05
L19	6	"6952043"	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/12/09 17:11
L20	952	438/200.ccls.	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/12/09 17:17

### EAST Search History

L21	2174	438/197.ccls.	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/12/09 17:17
L22	274	438/237.ccls.	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/12/09 17:17
L23	8	20 and etch\$3 with pillar	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/12/09 17:17
L24	23	21 and etch\$3 with pillar	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/12/09 17:17
L25	5	22 and etch\$3 with pillar	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/12/09 17:17

### EAST Search History

S1	2942	etch\$3 with pillar	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/12/23 19:10
S2	206	S1 and etch\$3 with strip	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/12/23 19:11
S3	25	S2 and second adj etch\$3 with pillar	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/12/23 19:38
S4	2	("20020028541").PN.	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/12/23 19:33
S5	20	S3 and antifuse	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/12/23 19:39

## EAST Search History

S6	250810	((first with (mask or photoresist or resist or pattern)) same (second with (mask or resist or photoresist or pattern)))	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/06/16 18:28
S7	39871	((first with (mask or photoresist or resist or pattern)) same (second with (mask or resist or photoresist or pattern)) same different)	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/06/16 18:28
S8	0	((first with (mask or photoresist or resist or pattern)) same (second with (mask or resist or photoresist or pattern)) same different same (back adj to adj back))	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/06/16 18:28
S9	1611	((first with (mask or photoresist or resist or pattern)) same (second with (mask or resist or photoresist or pattern)) same different same (sequential\$3))	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/06/16 18:29
S10	604	((first with (mask or photoresist or resist or pattern)) same (second with (mask or resist or photoresist or pattern)) same different same (sequential\$3)) and semiconductor	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/06/16 18:30

## EAST Search History

S11	88	((first adj (mask or photoresist or resist or pattern)) same (second adj (mask or resist or photoresist or pattern)) same different same (sequential\$3)) and semiconductor	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/06/16 18:45
S12	0	S11 and antifuse	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/06/16 18:46
S13	5	S11 and pillar	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/06/16 18:49
S14	1365	pillar with memory	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/06/16 18:59
S15	5	S13 and semiconductor and etch\$4	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/06/16 18:50

### EAST Search History

S16	862	S14 and semiconductor and etch\$4	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/06/16 18:50
S17	41	pillar with memory and etch\$4 with second adj direction	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/06/16 19:00